

HAT2208R

Silicon N Channel Power MOS FET Power Switching

REJ03G1595-0201 Rev.2.01 Nov.25.2016

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)} \! = 19.0 \; m\Omega$ typ. (at $V_{GS} \! = 10 \; V)$

Outline

RENESAS Package code: PRSP0008DD-D (Package name: SOP-8<FP-8DAV>)

8765

BDDDDD

1, 2, 3 Source
4 Gate
5, 6, 7, 8 Drain

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	9	А
Drain peak current	I _{D(pulse)} Note1	72	А
Body-drain diode reverse drain current	I _{DR}	9	А
Avalanche current	I _{AP} Note 2	9	А
Avalanche energy	E _{AR} Note 2	8.1	mJ
Channel dissipation	Pch Note3	2.0	W
Channel to ambient thermal impedance	θch-a Note3	62.5	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tch = 25°C, Rg \geq 50 Ω
- 3. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10s

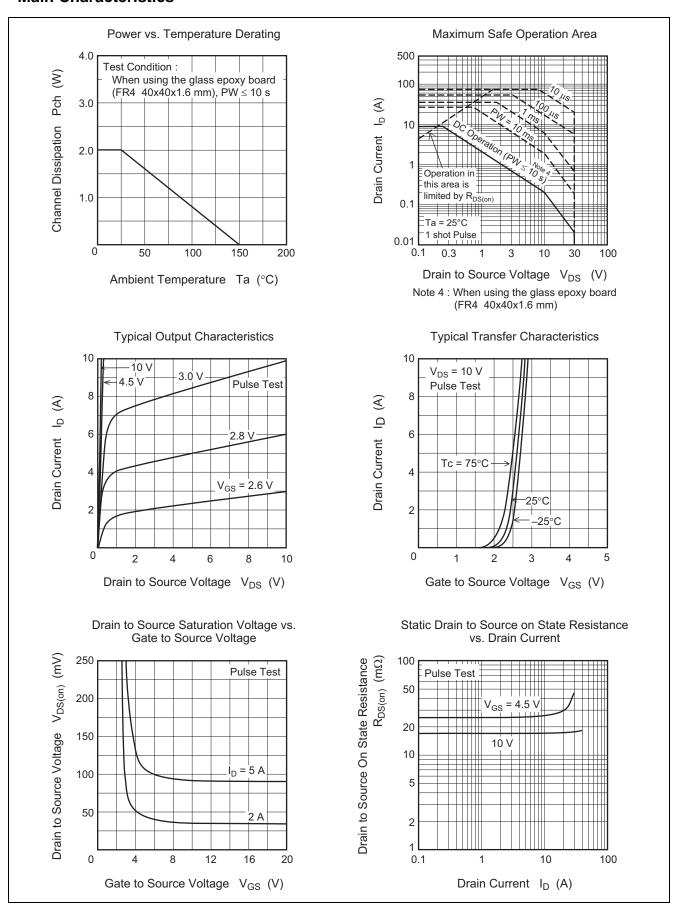
Electrical Characteristics

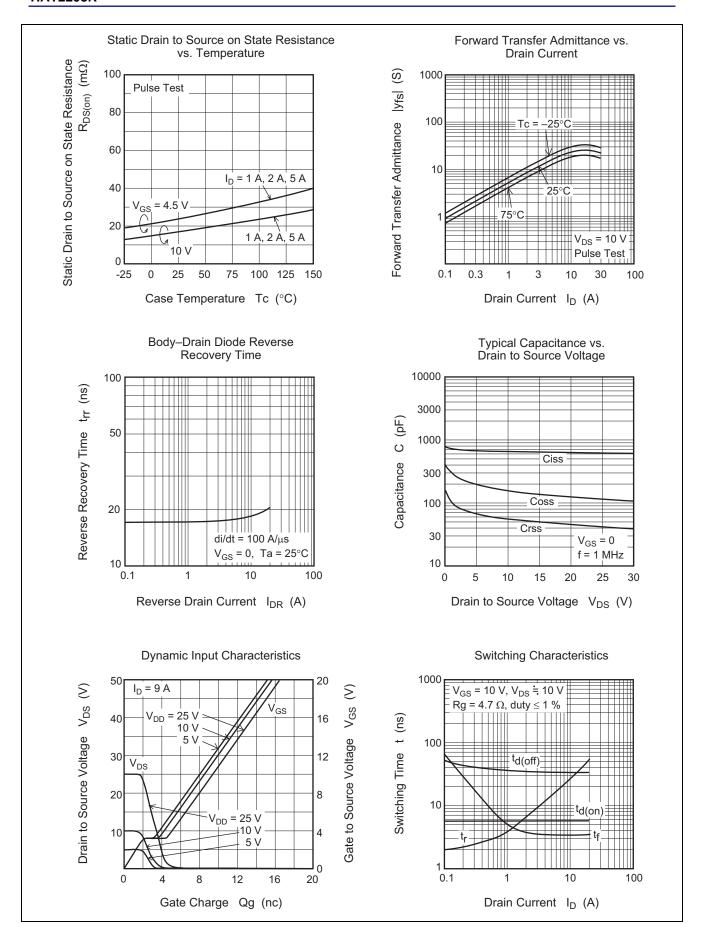
 $(Ta = 25^{\circ}C)$

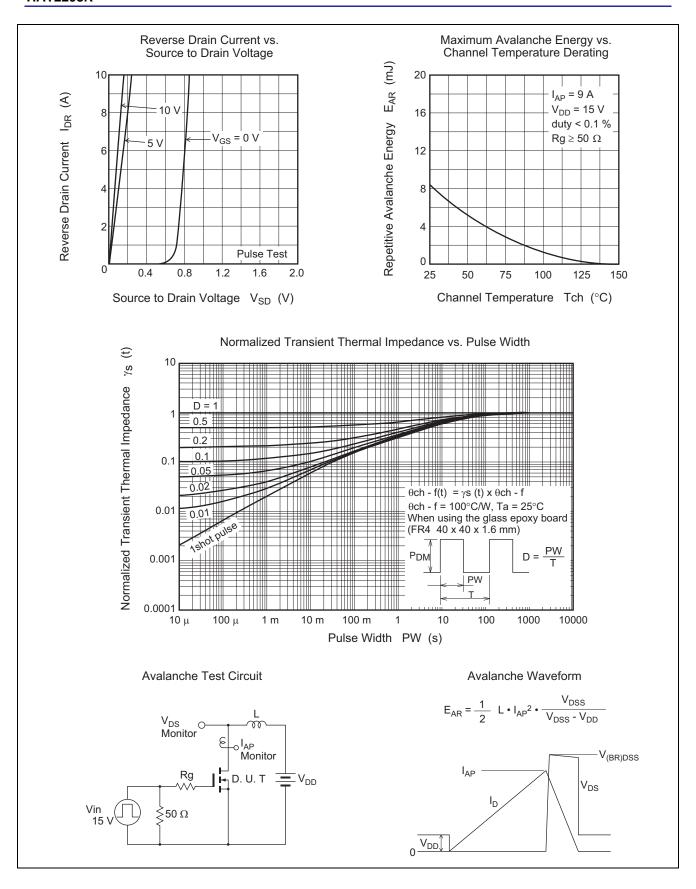
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}		_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	_	2.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}		19	24	mΩ	$I_D = 4.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R _{DS(on)}		24	35	mΩ	$I_D = 4.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	9.5	16	_	S	$I_D = 4.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss		630	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	160	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	56	_	pF	
Gate Resistance	Rg	_	1.1	_	Ω	
Total gate charge	Qg	_	4.4	_	nC	V _{DD} = 10 V
Gate to source charge	Qgs	_	2.2	_	nC	V _{GS} = 4.5 V I _D = 9 A
Gate to drain charge	Qgd	_	1.4	_	nC	
Turn-on delay time	t _{d(on)}	_	5.8	_	ns	V _{GS} = 10 V, I _D = 4.5 A
Rise time	t _r	_	15	_	ns	$V_{DD} \cong 10 \text{ V}$
Turn-off delay time	t _{d(off)}	_	34	_	ns	$R_L = 2.22 \Omega$
Fall time	t _f	_	3.5	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	_	0.84	1.10	V	IF = 9 A, V _{GS} = 0 ^{Note4}
Body-drain diode reverse recovery	t _{rr}	_	18	_	ns	IF = 9 A, V _{GS} = 0
time						di _F / dt = 100 A/ μs

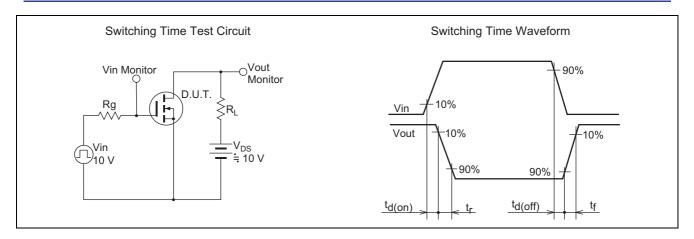
Notes: 4. Pulse test

Main Characteristics

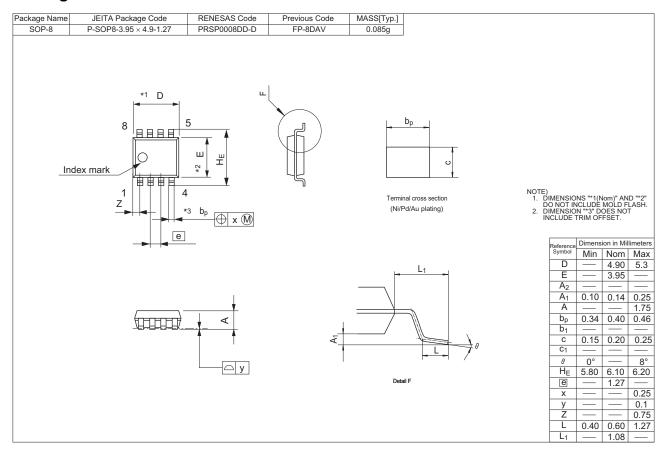








Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
HAT2208R-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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